

# Cypress Semiconductor Product Qualification Report

QTP# 000603 VERSION 2.0  
October, 2003

<b>Full Speed USB Microcontrollers</b> 0.5um TLM Technology, Fab HME	
<b>AN2122TC/ AN2126TC</b> <b>AN2122SC/ AN2126SC</b>	<b>EZ-USB™ Series 2100</b> <b>Family</b>

## CYPRESS TECHNICAL CONTACT FOR QUALIFICATION DATA:

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### PRODUCT QUALIFICATION HISTORY

<b>Qual Report</b>	<b>Description of Qualification Purpose</b>	<b>Date Comp</b>
001004	New 0.5um TLM Technology/New CY7C09449PV-AC Product Qualification	Aug 00
000603	New AN2122SC Product and bond options, 0.5um TLM Technology	Oct 00

<b>PRODUCT DESCRIPTION (for qualification)</b>	
Qualification Purpose: To qualify AN2122SC and its product family in qualified 0.5umTLM Technology, Fab HME	
Marketing Part #:	AN2122SC/AN2126SC, AN2122TC/2126TC
Device Description:	3.3V, Full Speed Microcontroller, Commercial available in 44-pin / 80-pin PQFP Package.
Cypress Division:	Cypress Semiconductor Corporation – Interface Product Division (IPD)
Overall Die (or Mask) REV:	Rev. A
What ID markings on Die:	GVS793K8

<b>TECHNOLOGY/FAB PROCESS DESCRIPTION</b>			
Number of Metal Layers:	3	Metal Composition:	Metal 1: (Ti/TiN)/Ti/Al-1%Si-0.5%Cu/Ti/TiN Metal 2: (Ti/TiN)/Ti/Al-1%Si-0.5%Cu/Ti/TiN Metal 3: (Ti/TiN)/Ti/Al-1%Si-0.5%Cu/TiN
Passivation Type and Materials:	Silicon Nitride		
Free Phosphorus contents in top glass layer (%)	Zero		
Generic Process Technology/Design Rule ( $\mu$ -drawn):	CMOS / 0.5 micron		
Gate Oxide Material/Thickness (MOS):	SiO <sub>2</sub> / 95 A		
Name/Location of Die Fab (prime) Facility:	Hyundai / Cheong Ju, Korea		
Die Fab Line ID/Wafer Process ID:	CF4 / HL50 (Hyundai)		

**PACKAGE AVAILABILITY**

<b>PACKAGE TYPE</b>	<b>ASSEMBLY SITE FACILITY</b>
<b>44-pin/ 80-pin PQFP</b>	<b>Hyundai-Korea (HME)</b>

**Note:** Package Qualification details upon request

<b>MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION</b>	
<b>Package Outline, Type, or Name:</b>	44-pin Plastic Quad Flatpack (PQFP)
<b>Mold Compound Name/Manufacturer:</b>	LMC-400V
<b>Mold Compound Flammability Rating:</b>	V-O per UL 94
<b>Oxygen Rating Index:</b>	>28%
<b>Lead Frame Material:</b>	Alloy 42
<b>Lead Finish, Composition / Thickness:</b>	Solder Plate, 85%Sn, 15%Pb
<b>Die Backside Preparation Method/Metallization:</b>	N/A
<b>Die Separation Method:</b>	Wafer Saw
<b>Die Attach Supplier:</b>	Ablestik
<b>Die Attach Material:</b>	84-1 LMISR4
<b>Wire Bond Method:</b>	Thermosonic
<b>Wire Material/Size:</b>	Au, 1.3um
<b>Thermal Resistance Theta JA °C/W:</b>	33°C/W
<b>Package Cross Section Yes/No:</b>	N/A
<b>Assembly Process Flow:</b>	Hyundai-turn-key
<b>Name/Location of Assembly (prime) facility:</b>	Hyundai-Korea (HME)

<b>ELECTRICAL TEST / FINISH DESCRIPTION</b>	
<b>Test Location:</b>	Hyundai-Korea (HME)
<b>Fault Coverage:</b>	100%

**RELIABILITY TESTS PERFORMED PER SPECIFICATION REQUIREMENT**

Stress/Test	Test Condition (Temp/Bias)	Result P/F
High Temperature Operating Life Early Failure Rate	Dynamic Operating Condition, Vcc =3.8V, 150C Dynamic Operating Condition, Vcc = 3.8V, 135°C	P
High Temperature Operating Life Latent Failure Rate	Dynamic Operating Condition, Vcc =3.8V, 150C Dynamic Operating Condition, Vcc = 3.8V, 135°C	P
Temperature Cycle	MIL-STD-883C, Method 1010, Condition C, -65°C to 150°C Precondition: JESD22 Moisture Sensitivity MSL 3 192 Hrs., 30°C/60%RH+3IR-Reflow, 220°C+5, -0°C	P
Pressure Cooker Test	121°C, 100%RH Precondition: JESD22 Moisture Sensitivity MSL 3 192 Hrs., 30°C/60%RH+3IR-Reflow, 220°C+5, -0°C	P
Electrostatic Discharge Human Body Model (ESD-HBM)	2,200V, 1,100V MIL-STD-883, Method 3015.7	P
Electrostatic Discharge Charge Device Model (ESD-CDM)	500V Cypress Spec. 25-00020	P
Latchup Sensitivity	125C, 10V, ±300mA In accordance with JEDEC 17. Cypress Spec. 01-00081	P

**RELIABILITY FAILURE RATE SUMMARY**

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal AF <sup>3</sup>	Failure Rate
High Temperature Operating Life Early Failure Rate	858	0	N/A	N/A	0 PPM
High Temperature Operating Life <sup>1,2</sup> Long Term Failure Rate	173,408 DHRs	0	0.7	88-170	45 FIT

<sup>1</sup> Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.

<sup>2</sup> Chi-squared 60% estimations used to calculate the failure rate.

<sup>3</sup> Thermal Acceleration Factor is calculated from the Arrhenius equation

$$AF = \exp \left[ \frac{E_A}{k} \left[ \frac{1}{T_2} - \frac{1}{T_1} \right] \right]$$

where:

E<sub>A</sub> =The Activation Energy of the defect mechanism.

k = Boltzmann's constant = 8.62x10<sup>-5</sup> eV/Kelvin.

T<sub>1</sub> is the junction temperature of the device under stress and T<sub>2</sub> is the junction temperature of the device at use conditions.

## Reliability Test Data

QTP #: 000603

<b>Device</b>	<b>Fab Lot #</b>	<b>Assy Lot #</b>	<b>Assy Loc</b>	<b>Duration</b>	<b>Samp</b>	<b>Rej</b>	<b>Failure Mechanism</b>
<b>STRESS: HIGH TEMP DYNAMIC OPERTING LIFE - EARLY FAILURE RATE, 150C, 3.8V, VCC MAX</b>							
AN2122SC-NC	NY0738	OM26		48	858	0	
<b>STRESS: HIGH TEMP DYNAMIC OPERTING LIFE-LATENT FAILURE RATE, 150C, 3.8V, Vcc Max</b>							
AN2122SC-NC	NY0738	OM26		80	146	0	
AN2122SC-NC	NY0738	OM26		500	116	0	
<b>STRESS: ESD-CHARGE DEVICE MODEL, 1000V</b>							
AN2122SC-NC	NY0436	GL09/16		COMP	3	0	
<b>STRESS: ESD- HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 1,100V</b>							
AN2122SC-NC	NY0436	GL09/16		COMP	3	0	
<b>STRESS: STATIC LATCH-UP TESTING, 125C, 10V, +/-300mA</b>							
AN2122SC-NC	NY0738	OM26		COMP	3	0	
<b>STRESS: PRESSURE COOKER TEST, 121C, 100%RH), PRE COND 192HRS 30C/60%RH, MSL3</b>							
AN2122SC-NC	NY0436	GL09/16		168	50	0	
<b>STRESS: TC CONDITION C, -65C TO 150C, PRE COND. 192 HRS 30C/60% RH, MSL3</b>							
AN2122SC-NC	NY0436	GL09/16		300	50	0	
AN2122SC-NC	NY0738	OM26		500	48	0	

## Reliability Test Data

QTP #: 001004

<i>Device</i>	<i>Fab Lot #</i>	<i>Assy Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
<b>STRESS: HIGH TEMP DYNAMIC OPERTING LIFE - EARLY FAILURE RATE, 135C, 3.8V, VCC MAX</b>							
CY7C09449PV-AC		800001208	SEOL-L	96	140	0	
CY7C09449PV-AC		800001208/2791	SEOL-L	96	488	0	
CY7C09449PV-AC		800002104	SEOL-L	96	1196	1	*UNKNOWN, NOT VISUAL
<b>STRESS: HIGH TEMP DYNAMIC OPERTING LIFE-LATENT FAILURE RATE, 135C, 3.8V, Vcc Max</b>							
CY7C09449PV-AC		800002104	SEOL-L	168	118	0	
CY7C09449PV-AC		800002104	SEOL-L	1000	112	0	
<b>STRESS: ESD-CHARGE DEVICE MODEL, 750V</b>							
CY7C09449PV-AC		800002104	SEOL-L	COMP	3	0	
<b>STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2,200V</b>							
CY7C09449PV-AC		800002104	SEOL-L	COMP	3	0	
<b>STRESS: STATIC LATCH-UP TESTIN,, 125C, 10V, +/-300mA</b>							
CY7C09449PV-AC		800002104	SEOL-L	COMP	3	0	
<b>STRESS: PRESSURE COOKER TES, 121C, 100%RH, PRE COND 192HRS 30C/60%RH, MSL3</b>							
CY7C09449PV-AC		800002104	SEOL-L	168	47	0	
<b>STRESS: TC CONDITION C, -65C TO 150C, PRE COND. 192 HRS 30C/60% RH, MSL3</b>							
CY7C09449PV-AC		800002104	SEOL-L	300	48	0	
CY7C09449PV-AC		800002104	SEOL-L	500	47	0	
CY7C09449PV-AC		800002104	SEOL-L	1000	45	0	

\*A CAR #20001905 was issued to HME